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IN THE UNITED STATES PATENT AND
TRADEMARK OFFICE

Phoenix, Arizona

Applicant: James A. Cox et al. **Group:** 2874
Serial No.: 10/028,437 **Examiner:** Not assigned
Filed: 12-28-2001 **Atty Docket No.:** V637 02531 US
For: VERTICAL CAVITY SURFACE EMITTING LASER HAVING A
GAIN GUIDE APERTURE INTERIOR OF AN OXIDE
CONFINEMENT LAYER

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(37 C.F.R. 1.97(b)(3))Before Mailing of a first Office action)

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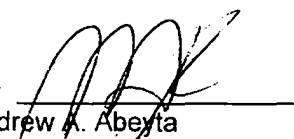
2. Form PTO-1449, List of Prior Art Cited by Applicant, citing fifteen U.S. patents, no foreign patents, and twenty-four publications.

3. These references are in addition to those listed in the Supplemental Information Disclosure Statements and Form PTO 1449 filed with the Patent and Trademark Office on May 14, 2003, and December 28, 2001.

4. The person making this statement is the attorney who signs below on the basis of the information supplied by the inventor(s) and the information in the attorney's file.

5. Because this Supplement Information Disclosure Statements is filed in accordance with 37 CFR 1.97(b)(3), before mailing date of first office action, no fees are due.

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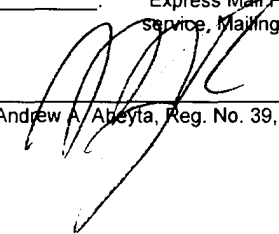
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Sheet 1 Of 3

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Application Number	10/028,437
Filing Date	12-28-2001
First Named Inventor	James A. Cox et al.
Art Unit	2874
Examiner Name	t.b.d.
Attorney Docket Number	V637 02531 US

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pp, Columns, Lines where relevant passages or relevant figures appear
		Number	Kind Code ² (if known)			
		5,262,360	A	Holonyak, Jr., et al.	11-16-1993	
		5,373,522	A	Holonyak, Jr., et al.	12-13-1994	
		5,493,577	A	Choquette et al.	02-20-1996	
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		6,297,068	B1	Thornton	10-02-2001	
		6,372,533	B2	Jayaraman et al.	04-16-2002	

FOREIGN PATENT DOCUMENTS

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First Named Inventor	James A. Cox et al.
Art Unit	2874
Examiner Name	t.b.d.
Attorney Docket Number	V637 02531 US

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and-or country where published	T ²
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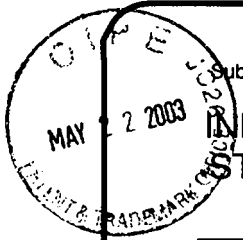
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